

Datasheet

Trench gate field-stop, 1350 V, 35 A, soft-switching IH2 series IGBT in a TO-247 long leads package



G(1) O E(3)

NG1E3C2T

Features

- Designed for soft commutation only
- Maximum junction temperature: T_J = 175 °C
- Low V_{CE(sat)} = 1.75 V (typ.) @ I_C = 30 A
- Very low V_F and soft-recovery co-packaged diode
- · Minimized tail current
- · Tight parameter distribution
- · Low thermal resistance
- Positive temperature coefficient

Applications

- · Induction heating
- · Resonant converters
- · Microwave ovens

Description

The newest IGBT 1350 V IH2 soft-switching series has been developed using an advanced proprietary trench gate field-stop structure, whose performance is optimized both in conduction and in switching energy losses for soft-switching applications. A freewheeling diode with a very low drop forward voltage is copackaged. The result is a product specifically designed to maximize efficiency for any resonant and soft-switching applications.

Product status link STGWA35IH135DLF2

Product summary			
Order code STGWA35IH135DLF2			
Temperature range	G35IH135DLF2		
Package	TO-247 long leads		
Packing Tube			



1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CES}	Gate-source voltage	1350	V
l _a	Continuous collector current at T _C = 25 °C	70	A
I _C	Continuous collector current at T _C = 100 °C	35	_ A
I _{CP} ⁽¹⁾	Pulsed collector current	140	А
V_{GE}	Gate-emitter voltage	±20	V
I _F	Continuous forward current at T _C = 25 °C	70	A
'F	Continuous forward current at T _C = 100 °C	35	
I _{FP} ⁽¹⁾	Pulsed forward current	140	А
P _{TOT}	Total power dissipation at T _C = 25 °C	365	W
T _{stg}	Storage temperature range	-55 to 150	°C
TJ	Operating junction temperature range	-55 to 175	°C

^{1.} Pulse width is limited by maximum junction temperature.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
P	Thermal resistance junction-case IGBT	0.41	
R _{thJC}	Thermal resistance junction-case diode	1.47	°C/W
R _{thJA}	Thermal resistance junction-ambient	50	

DS12545 - Rev 1 page 2/10



2 Electrical characteristics

T_C = 25 °C unless otherwise specified

Table 3. Static characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)CES}	Collector-emitter breakdown voltage	V _{GE} = 0 V, I _C = 1 mA	1350			V
	$V_{GE} = 15 \text{ V, } I_{C} = 30 \text{ A}$	V _{GE} = 15 V, I _C = 30 A		1.75		
V _{CE(sat)} Collector-emitter saturation voltage	V_{GE} = 15 V, I_{C} = 30 A, T_{J} = 125 °C		1.95			
	V_{GE} = 15 V, I_{C} = 30 A, T_{J} = 175 °C		2.05		V	
	V _{GE} = 15 V, I _C = 60 A		2.30			
		I _F = 30 A		1.20		
V	Forward on-voltage	I _F = 30 A, T _J = 125 °C		1.20		V
V _F		I _F = 30 A, T _J = 175 °C		1.25		
		I _F = 60 A		1.55		
V _{GE(th)}	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 1 \text{ mA}$	5	6	7	V
I _{CES}	Collector cut-off current	V _{GE} = 0 V, V _{CE} = 1350 V			25	μA
I _{GES}	Gate-emitter leakage current	V _{CE} = 0 V, V _{GE} = ±20 V			±250	nA

Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{ies}	Input capacitance	V _{CE} = 25 V, f = 1 MHz,	-	3140	-	pF
C _{oes}	Output capacitance	$V_{GE} = 23 \text{ V}, 1 - 1 \text{ Will 12},$ $V_{GF} = 0 \text{ V}$	-	125	-	pF
C _{res}	Reverse transfer capacitance	VGE V	-	77	-	pF
Qg	Total gate charge	$V_{CC} = 600 \text{ V}, I_{C} = 30 \text{ A},$	-	255	-	nC
Q _{ge}	Gate-emitter charge	V _{GE} = 0 to 15 V	-	30	-	nC
Q _{gc}	Gate-collector charge	(see Figure 3. Gate charge test circuit)	-	124	-	nC

Table 5. Switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(off)}	Turn-off delay time	V _{CC} = 600 V, I _C = 30 A,	-	252	-	ns
t _f	Current fall time	$R_G = 10 \Omega$, $V_{GE} = 15 V$	-	111	-	ns
E _{off} ⁽¹⁾	Turn-off switching energy	(see Figure 1. Test circuit for inductive load switching)	-	1.42	-	mJ

DS12545 - Rev 1 page 3/10



Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(off)}	Turn-off delay time	V _{CC} = 600 V, I _C = 30 A,	-	300	-	ns
t _f	Current fall time	$R_G = 10 \Omega$, $V_{GE} = 15 V$,	-	247	-	ns
		T _J = 175 °C				
E _{off} ⁽¹⁾	Turn-off switching energy	(see Figure 1. Test circuit for inductive load switching)	-	2.46	-	μJ

^{1.} Including the tail of the collector current.

Table 6. IGBT switching characteristics (snubbed inductive load)

Symbol	Parameter	Test conditions ⁽¹⁾	Min.	Тур.	Max.	Unit
E _{off} ⁽²⁾		V_{CC} = 900 V, R_{G} = 10 Ω ,				
	Turn-off switching energy	I _C = 60 A, L = 500 μH,	-	0.95	-	
		C _{snub} = 330 nF				m.1
		V_{CC} = 900 V, R_{G} = 10 Ω ,				mJ
		I _C = 60 A, L = 500 μH,	-	1.87	-	
		C _{snub} = 330 nF, T _J = 175 °C				

- 1. See Figure 2. Test circuit for snubbed inductive load switching
- 2. Including the tail of the collector current.

DS12545 - Rev 1 page 4/10



3 Test circuits

AM01504v1

Figure 2. Test circuit for snubbed inductive load switching

L=100µH

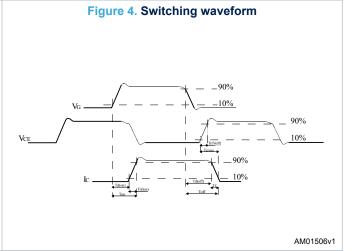
RG

D.U.T.

CSnub

AM17096v1

Figure 3. Gate charge test circuit $V_i \leq V_{\text{GMAX}} \qquad I_G = \text{CONST} \qquad 100 \ \Omega$ $Q = \frac{2200}{1 \ \text{k}\Omega} \qquad 100 \ \Omega$ $Q = \frac{2200}{1 \ \text{k}\Omega} \qquad Q = \frac{100 \ \Omega}{1 \ \text{k}\Omega}$



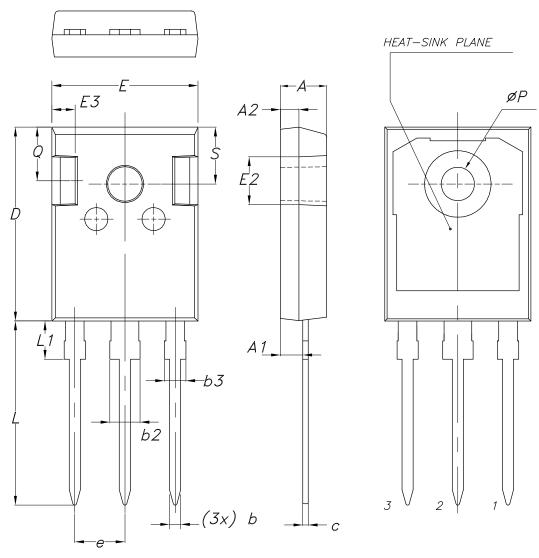
DS12545 - Rev 1 page 5/10

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 TO-247 long leads package information

Figure 5. TO-247 long leads package outline



8463846_2_F

DS12545 - Rev 1 page 6/10

Table 7. TO-247 long leads package mechanical data

Dim.		mm	
Dilli.	Min.	Тур.	Max.
Α	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.26
b2			3.25
b3			2.25
С	0.59		0.66
D	20.90	21.00	21.10
E	15.70	15.80	15.90
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
е	5.34	5.44	5.54
L	19.80	19.92	20.10
L1			4.30
Р	3.50	3.60	3.70
Q	5.60		6.00
S	6.05	6.15	6.25

DS12545 - Rev 1 page 7/10



Revision history

Table 8. Document revision history

Date	Version	Changes
19-Apr-2018	1	Initial release. The document status is preliminary data.

DS12545 - Rev 1 page 8/10



Prerelease product(s)

Contents

1	Elec	etrical ratings	2
2	Elec	etrical characteristics	3
3	Test	circuits	5
4	Pack	kage information	6
	4.1	TO-247 long leads package information	6
Rev	ision	history	8



IMPORTANT NOTICE - PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2018 STMicroelectronics - All rights reserved

DS12545 - Rev 1 page 10/10